

View Online at <https://aerobasegroup.com/nsn/5980-01-128-6263>

General Description:

Gallium arsenide infrared emitting diode coupled with a silicon high voltage photo-transistor in a dual-in-line pkg; 6 terminals; 0.330 in. Min to 0.350 in. Maximum Ig; photo-transistor has 300.0 mw, 300.0 vcer, 300.0 vcbo, 7.0 veco, 100.0 ma

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

A23900